

**Amendments to the Claims**

Claims 1-59 (Cancelled).

60. (Currently amended) A semiconductor processing method of depositing SiO<sub>2</sub> on a substrate comprising:

providing a substrate within a cold-wall chemical vapor deposition reactor;

providing rf power of 600W and a temperature of about 400°C within the chemical vapor deposition reactor;

injecting ~~liquid~~ TEOS into the chemical vapor deposition reactor at 975 sccm;

providing O<sub>2</sub> into the reactor at 600 sccm without passing through an ozone generator;

providing He into the reactor at 775 sccm;

feeding gaseous H<sub>2</sub>O<sub>2</sub> into the chemical vapor deposition reactor; and

decomposing the TEOS to form SiO<sub>2</sub> and depositing the SiO<sub>2</sub> onto the substrate; the decomposing being conducted at a pressure of from about 10 Torr to about 80 Torr.

61. (Previously presented) The semiconductor processing method of claim 60 wherein the gaseous H<sub>2</sub>O<sub>2</sub> and the TEOS are fed into the chemical vapor deposition reactor independently.

62. (Previously presented) The semiconductor processing method of claim 60 wherein the gaseous  $\text{H}_2\text{O}_2$  and the TEOS are fed into the chemical vapor deposition reactor simultaneously.

63. (Cancelled)

64. (Previously presented) The semiconductor processing method of claim 60 further comprising feeding gaseous  $\text{H}_2\text{O}$  into the chemical vapor deposition reactor.

65. (Cancelled)

66. (Previously presented) The semiconductor processing method of claim 60 wherein the surface of the substrate comprises a high aspect ratio topology and wherein the  $\text{SiO}_2$  is conformally deposited over the topology.

Claims 67-70 (Cancelled).